

In the Claims

Please cancel Claims 4 and 11-20.

Please amend Claims 1 and 5 and follows:

1. (Three times amended) An electrostatic discharge (ESD) protection structure for protecting an integrated circuit comprising:
- a first semiconductor region of a first conductivity type;
 - a second semiconductor region of a second conductivity type in contact with said first semiconductor region;
 - an electrically floating third semiconductor region of said first conductivity type in contact with said second semiconductor region and separated from said first semiconductor region by said second semiconductor region;
 - a fourth semiconductor region of said second conductivity type in contact with said third semiconductor region and separated from said second semiconductor region by said third semiconductor region; and
 - a fifth semiconductor region of said first conductivity type in contact with said fourth semiconductor region and separated from said third semiconductor region by said fourth semiconductor region; wherein a first terminal, A, of said ESD structure is connected to said first semiconductor region and said second conductor region and a second terminal, K, of said ESD structure is connected to said fourth semiconductor region and said fifth semiconductor region.

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5. (Amended) The ESD structure of Claim 1 wherein said third semiconductor region includes an n-well region formed in a p-type semiconductor substrate.

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